

Studies of tunnel MOS diodes I. Interface effects in silic

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Citation Report

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| 1505 | A Comparison Electronic Specifications of the MS & MPS type Schottky Diodes (SDs) via Utilizing Voltage-Current (V-I) Characteristics. <i>Gazi University Journal of Science Part A:engineering and Innovation</i> , 2023, 10, 62-69. | 0.2 | 1         |
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